

Abstract of the Disclosure:

A device for the sublimation growth of an SiC single crystal, with foil-lined crucible. The device for producing an SiC single crystal includes a crucible with a crucible inner zone.

5 Inside this zone, there is a storage area for storing a stock of solid SiC and a crystal area in which an SiC single crystal grows onto an SiC seed crystal. A heater device is arranged outside the crucible. On a side that faces the crucible inner zone, the crucible is lined with a foil of tantalum, tungsten, niobium, molybdenum, rhenium, iridium, ruthenium, hafnium or zirconium. As a result, the crucible is sealed and a reaction between the aggressive components of the SiC gas phase and the crucible wall is prevented.

MPW\vs